



30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

-24 A

Features

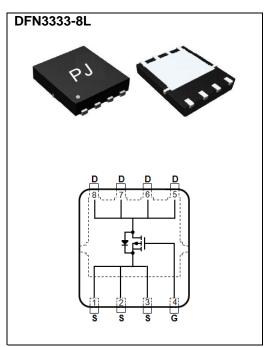
- R_{DS(ON)}, V_{GS}@-10V,I_D@-4A<30mΩ
- R_{DS(ON)}, V_{GS}@-4.5V,I_D@-2A<45mΩ
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.001 ounces, 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	-30	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	I _D	-24	А	
	T _C =100°C		-15		
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	-50	İ	
Power Dissipation	T _C =25°C	Po	30	W	
	Tc=100°C		12		
Continuous Drain Current	T _A =25°C	I _D	-6.5	Α	
	T _A =70°C		-5.0		
Power Dissipation	T _A =25°C	ב	2.0	W	
Power Dissipation	T _A =70°C	Pb	1.3		
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	$R_{ heta JC}$	4.2	20044	
	Junction to Ambient	$R_{\theta JA}$	62.5	°C/W	

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	BVDSS VGS=0V,ID=-250uA VGS(th) VDS=VGS,ID=-250uA		-	-	V
Gate Threshold Voltage	$V_{GS(th)}$			-1.6	-2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V,I _D =-4A	-	26	30	mΩ
		V _{GS} =-4.5V,I _D =-2A	-	36	45	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V,V _{GS} =0V	-	-	-1.0	uA
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic ^(Note 6)						
Total Gate Charge	Q_g	V _{DS} =-15V, I _D =-5A, V _{GS} =-4.5V ^(Note 1,2)	-	7.8	-	nC
Gate-Source Charge	Q_{gs}		-	2.7	-	
Gate-Drain Charge	Q_{gd}		-	2.8	-	
Input Capacitance	Ciss	\(\frac{1}{2}\)\(\frac{1}\)\(\frac{1}{2}\)\(\frac{1}{2}\)\(\frac{1}{2}\)\(\frac{1}{2}\)\(\frac{1}\)\(\frac{1}{2}\)\(\frac{1}\)\(\frac{1}\)\(\frac{1}\)\(\frac{1}\)\(\frac{1}\)\(\frac{1}\)\(\frac{1}\)\(\frac{1}\)\(\fra	-	870	-	pF
Output Capacitance	Coss	V _{DS} =-15V, V _{GS} =0V,	-	130	-	
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	93	-	
Turn-On Delay Time	td _(on)	A51/15 4A	-	6.5	-	
Turn-On Rise Time	tr	V _{DS} =-15V,ID=-1A,	-	8.8	-	ns
Turn-Off Delay Time	td _(off)	$V_{GS}=-10V$, $R_{G}=6\Omega$	-	73	-	
Turn-Off Fall Time	t _f	(14010-1,2)	-	44	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	1		-	-	-24	А
Diode Forward Current	Is					
Diode Forward Voltage	V _{SD}	Is=-1A,V _{GS} =0V	-	-0.75	-1	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

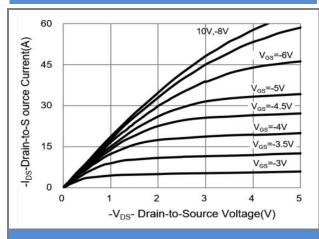


Fig.1 On-Region Characteristics

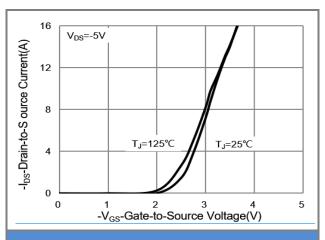


Fig.2 Transfer Characteristics

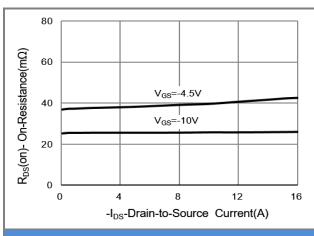


Fig.3 On-Resistance vs. Drain Current

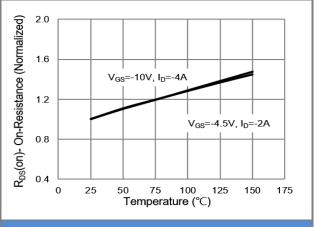
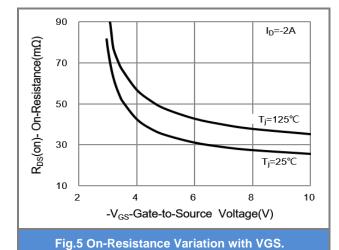


Fig.4 On-Resistance vs. Junction temperature



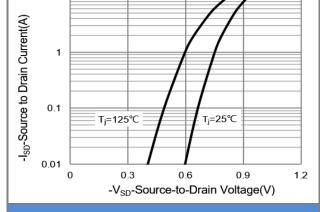


Fig.6 Source-Drain Diode Forward Voltage

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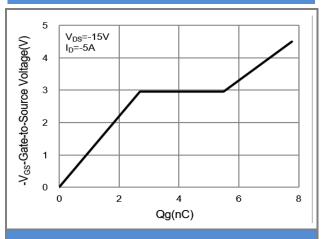


Fig.7 Gate-Charge Characteristics

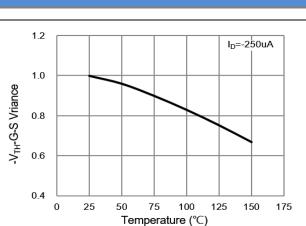


Fig.9 Threshold Voltage Variation with Temperature

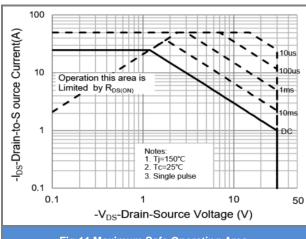


Fig.11 Maximum Safe Operating Area

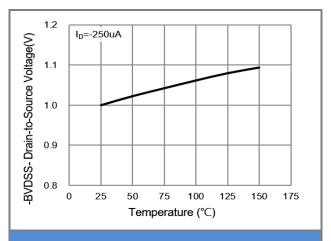


Fig.8 Breakdown Voltage Variation vs. Temperature.

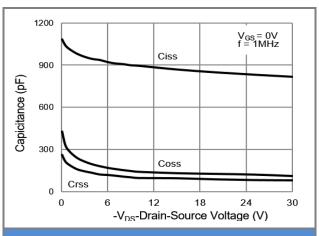


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

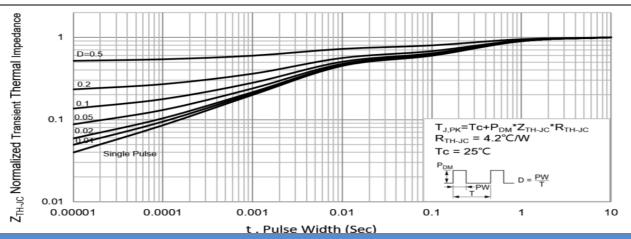


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

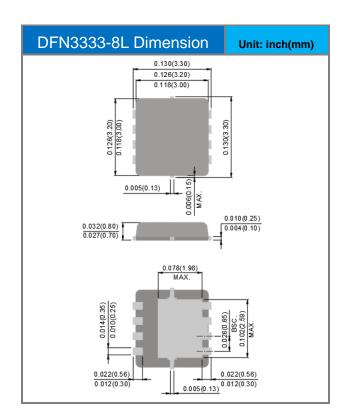


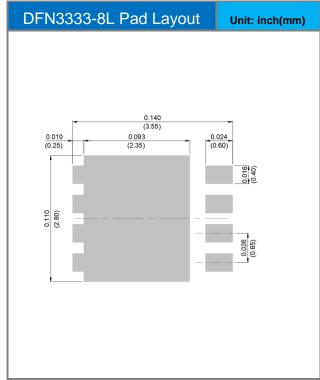


Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4409P_R2_00001	DFN3333-8L	5K pcs / 13" reel	4409	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout









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